

OPA6615

Super Bright

Red LED Chip

GaAlAs / GaAs

1. Material Substrate GaAs (P Type)
Epitaxial Layer GaAlAs (N/P Type)

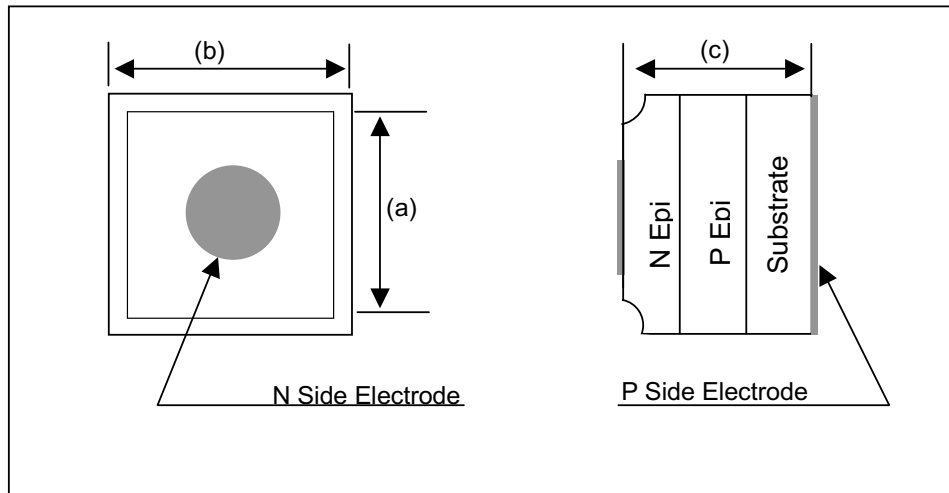
2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		1.8	2.2	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	5.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	450	650		mcd	$I_F=20\text{mA}$
Wavelength	Hue		645		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		20		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1³/₄ plastic package.

4. Mechanical Data (a) Emission Area ----- 12mil × 12mil
(b) Bottom Area ----- 14mil × 14mil
(c) Chip Thickness ----- 11mil



Knowledge*on Inc.

For more information, visit our website at www.knowledge-on.com

513-37 Eoyang-dong, Iksan, 570-210, Korea. Tel: +82-63-839-1111. Fax: +82-63-835-8259

